

CLAIMS

1. A transistor comprising elements of a bipolar static induction transistor disposed on both major surfaces of a silicon monocrystal substrate; an epitaxial layer, a gate, channels, sources, gate and source electrodes; impurity concentration near said gates is high enough: said gate, said channels, said sources are disposed in said epitaxial layer; donor concentration of said epitaxial layer equals of about 10.17 cm^{-3} ; donor concentration of said substrate equals of about 10.14 cm^{-3} ; one channel of the multielement structure is thicker than the other normally-off channels; said channel is connected to a separate electrode; said source electrodes are formed of n+-type polysilicon.

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